



## Product Overview

### NSS30201MR6T1G: Low $V_{CE(sat)}$ Transistor, NPN, 30 V, 2.0 A

For complete documentation, see the data sheet

#### Product Description

Low  $V_{CE(sat)}$  Bipolar Transistors are miniature surface mount devices featuring ultra low saturation voltage  $V_{CE(sat)}$  and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

#### Features

- High Current, Low  $V_{CE(sat)}$ , ESD Robust, High Current Gain, High Cut Off Frequency, Low Profile Package, Linear Gain (Beta)
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AECQ101 Qualified and PPAP Capable

#### Applications

- Load Switching, Battery Charging, External Pass Transistor, DC/DC Converter, Complimentary Driver, Current Extention & Low Drop Out Regulation, Cathode Florescent Lamp drive, Peripheral Driver - LEDs, Motors, Relays

#### Part Electrical Specifications

Product	Compliance	Status	Polarity	$I_C$ Continuous (A)	$V_{(BR)CEO}$ Min (V)	$V_{CE(sat)}$ Max (V)	$h_{FE}$ Min	$h_{FE}$ Max	$f_T$ Min (MHz)	$P_{TM}$ Max (W)	Package Type
NSS30201MR6T1G	AEC Qualified Pb-free Halide free	Active	NPN	2	30	0.2	300	900	200	1.75	TSOP-6
SNSS30201MR6T1G	AEC Qualified PPAP Capable Pb-free Halide free	Active	NPN	2	30	0.2	300	900	200	1.75	TSOP-6

For more information please contact your local sales support at [www.onsemi.com](http://www.onsemi.com)

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